UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO.

6,734,480 62

DATED

May 11, 2004

INVENTOR(S)

Chung et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

On the Cover Sheet:

Section 57, the Abstract, should read as follows:

Semiconductor capacitors comprise first electrodes, second electrodes, and tantalum oxide layers positioned between the first electrodes and the second electrodes. The tantalum oxide layers are formed by depositing at least one precursor and ozone gas, the at least one precursor represented by the formula:

$$H_3CH_2CO$$
 H_3CH_2CO
 H_3CH_2CO
 H_3CH_2CO
 H_3CH_2CO
 H_3CH_2CO
 H_3CH_2CO
 H_3CH_2CO
 H_3CH_2CO
 H_3CH_2CO

wherein X is selected from the group consisting of nitrogen, sulfur, oxygen, and a carbonyl group; and wherein R1 and R2 are independently alkyl.

MAILING ADDRESS OF SENDER: Myers, Bigel, Sibley & Sajovec P.O. Box 37428 Raleigh, NC 27627 PATENT NO. 6,734,480 No. of additional copies: ____

Burden Hour Statement: This form is estimated to take 1.0 hour to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, Patent and Trademark Office, Washington, DC 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Attention Certificate of Corrections Branch, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.